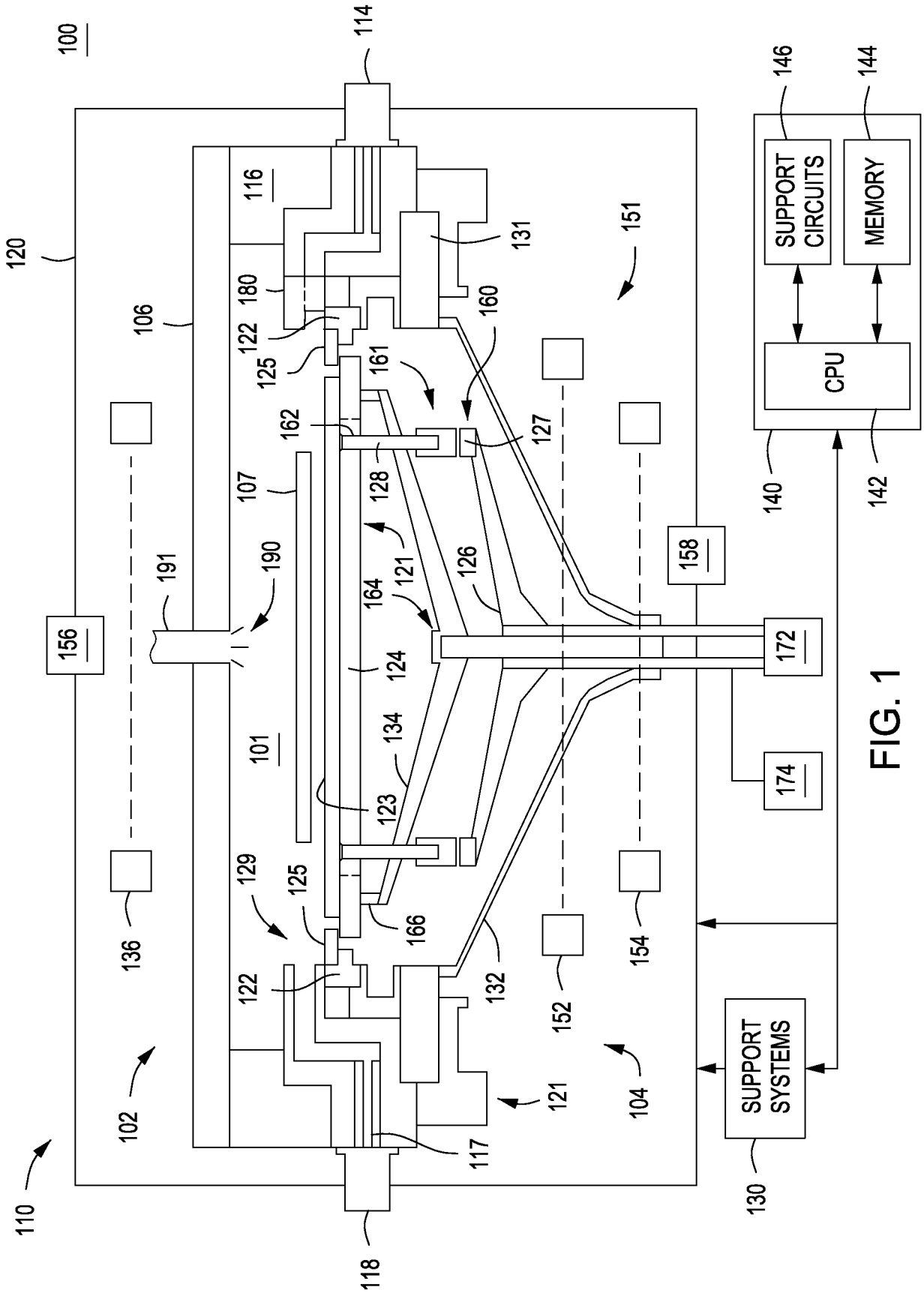

100
110
114
116
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174
180
190
191
SUPPORT CIRCUITS
MEMORY
CPU
SUPPORT SYSTEMS

FIG. 1

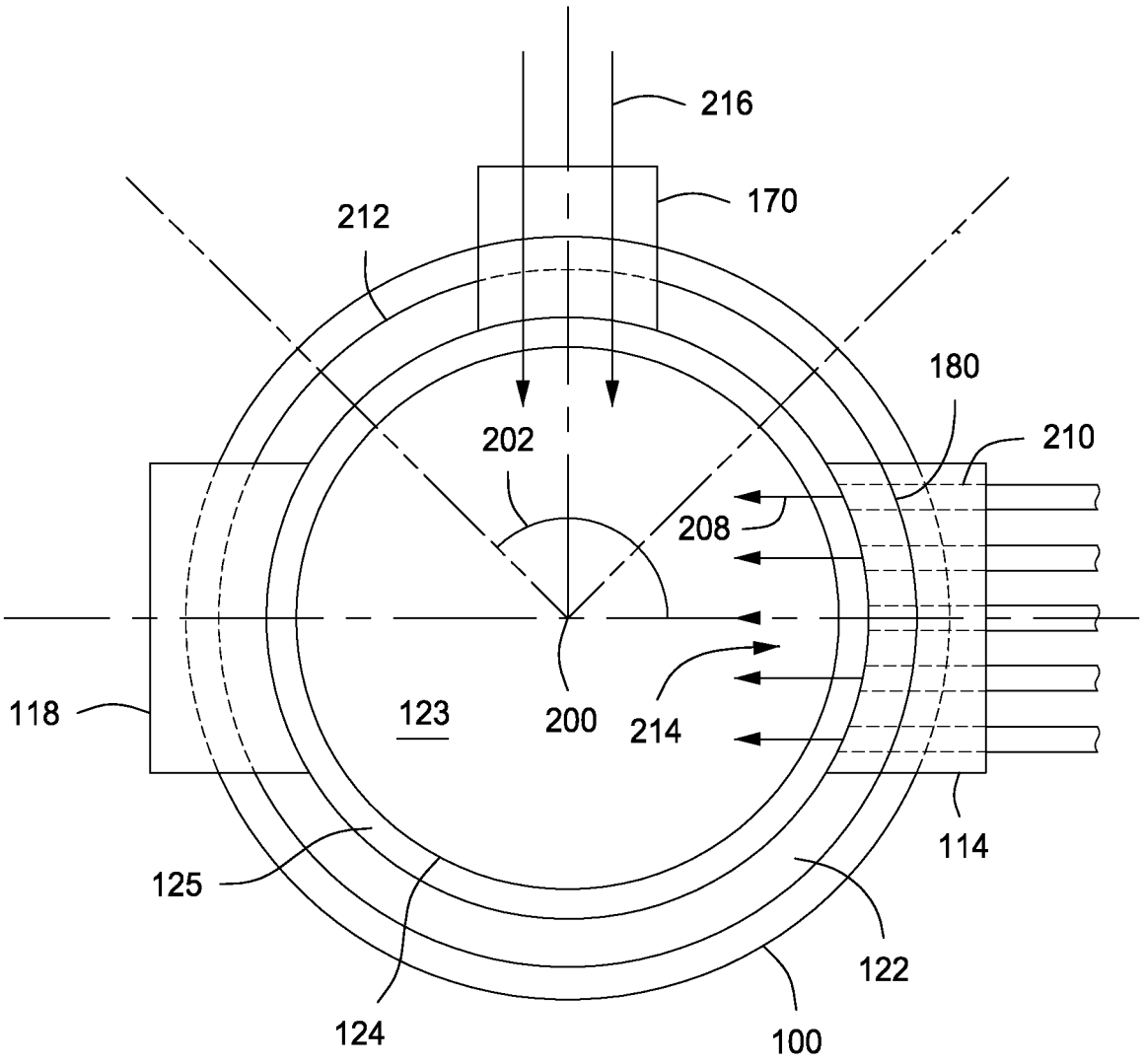


FIG. 2

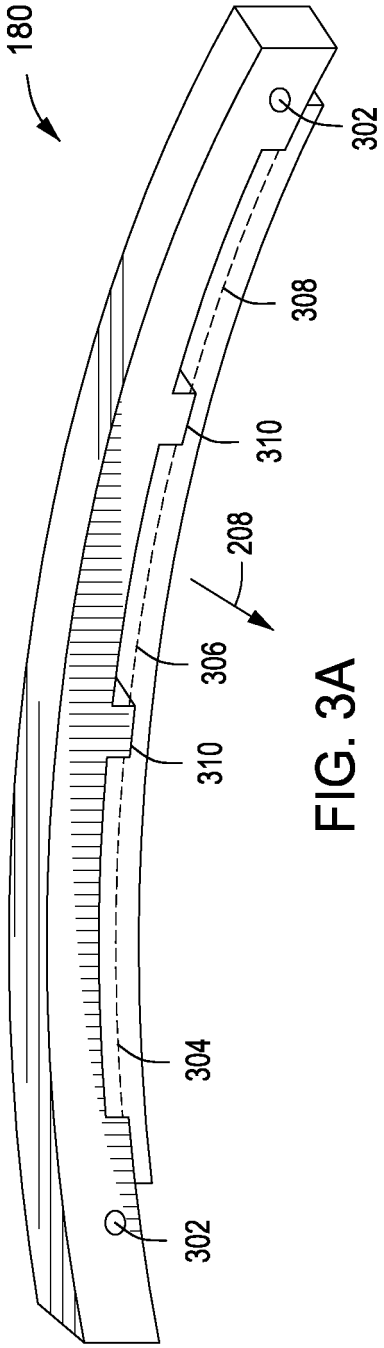

180
302
308
310
208
306
310
304
302

FIG. 3A

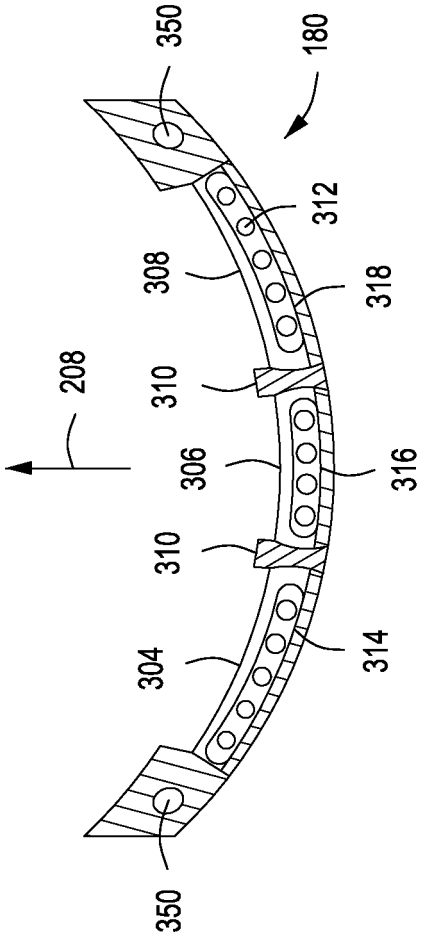

350
180
312
308
318
208
310
306
316
310
304
314
350

FIG. 3B

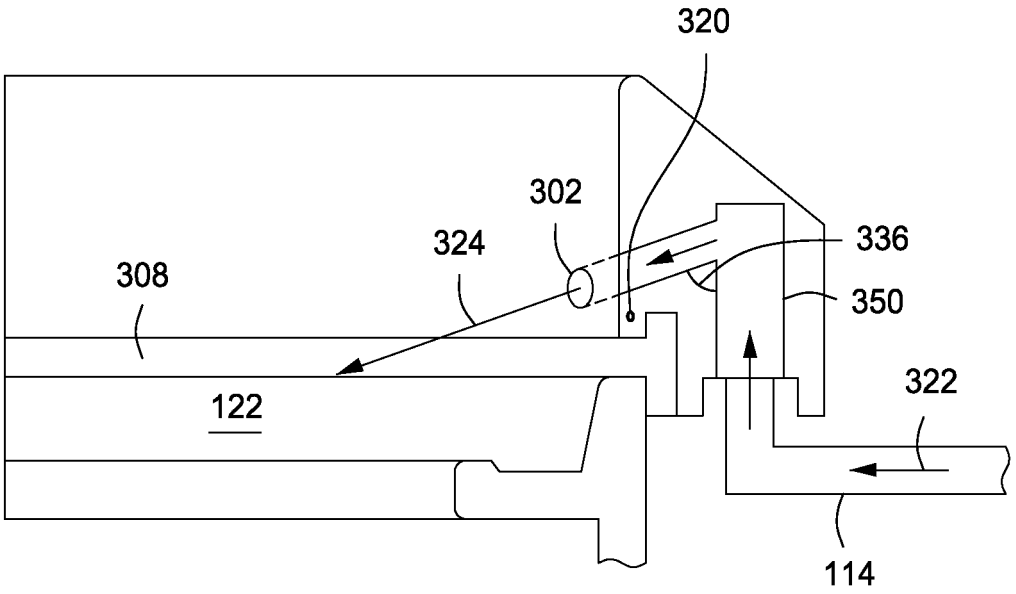

320
302
324
336
308
350
122
322
114

FIG. 3C

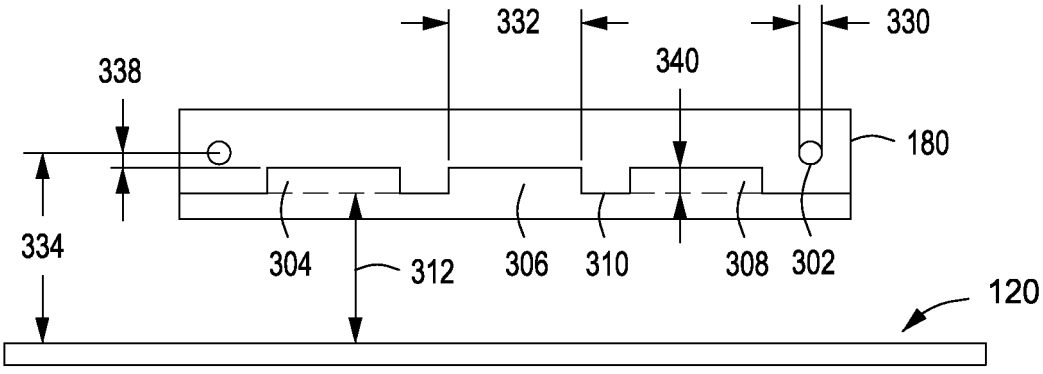

332
330
338
340
180
334
304
312
306
310
308
302
120

FIG. 3D

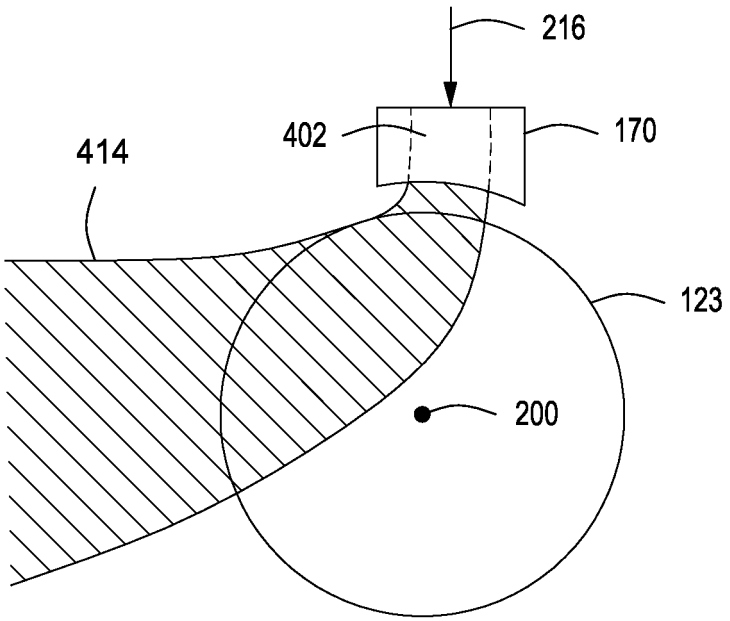


FIG. 4A

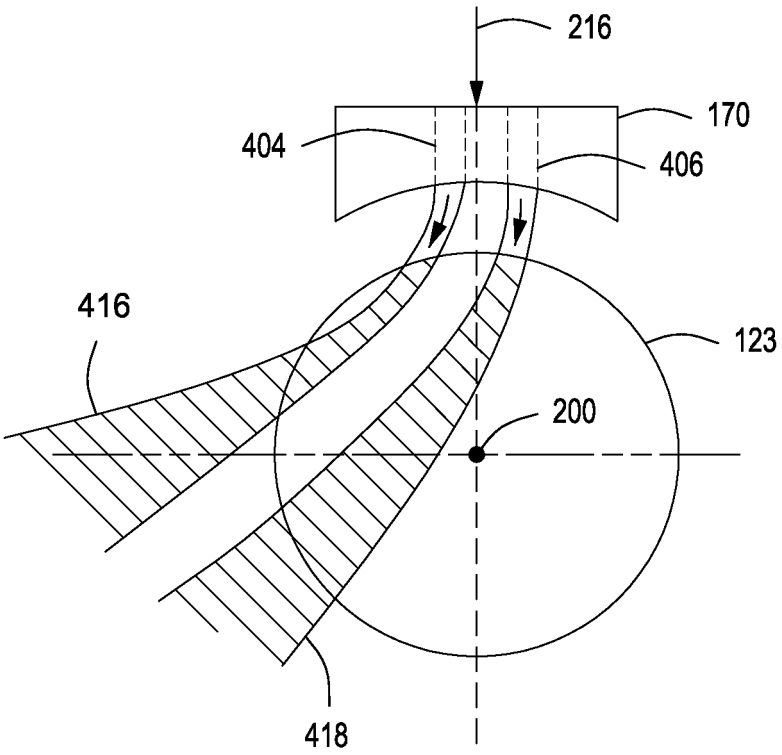


FIG. 4B

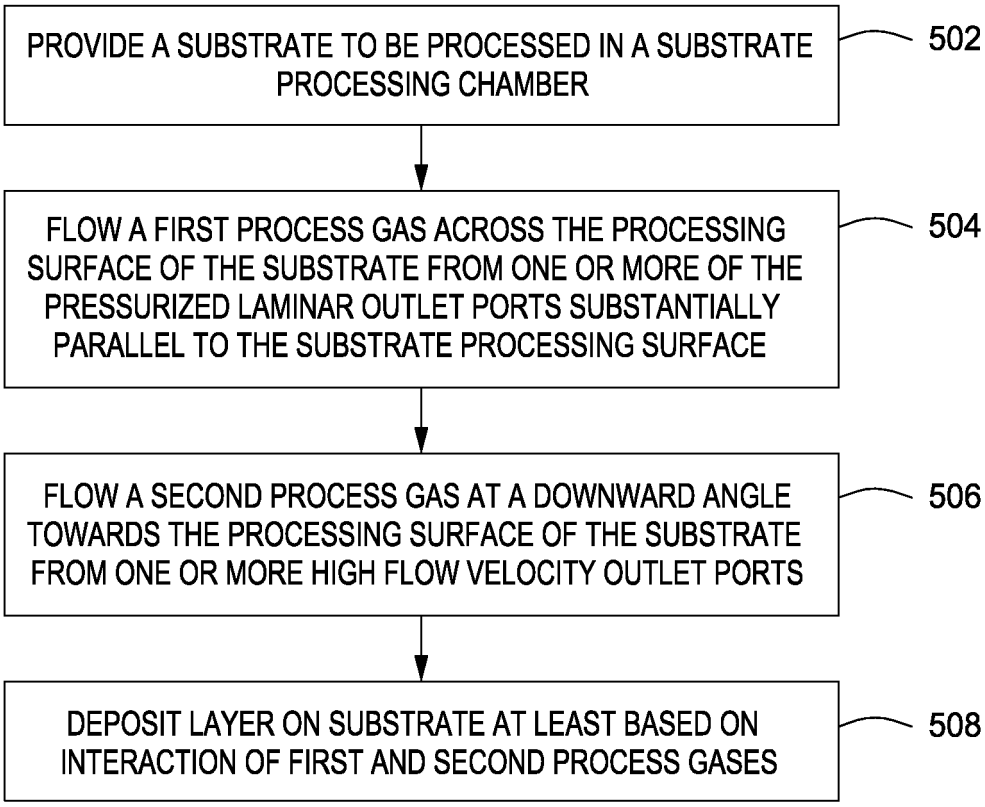

PROVIDE A SUBSTRATE TO BE PROCESSED IN A SUBSTRATE PROCESSING CHAMBER
502
FLOW A FIRST PROCESS GAS ACROSS THE PROCESSING SURFACE OF THE SUBSTRATE FROM ONE OR MORE OF THE PRESSURIZED LAMINAR OUTLET PORTS SUBSTANTIALLY PARALLEL TO THE SUBSTRATE PROCESSING SURFACE
504
FLOW A SECOND PROCESS GAS AT A DOWNWARD ANGLE TOWARDS THE PROCESSING SURFACE OF THE SUBSTRATE FROM ONE OR MORE HIGH FLOW VELOCITY OUTLET PORTS
506
DEPOSIT LAYER ON SUBSTRATE AT LEAST BASED ON INTERACTION OF FIRST AND SECOND PROCESS GASES
508

FIG. 5

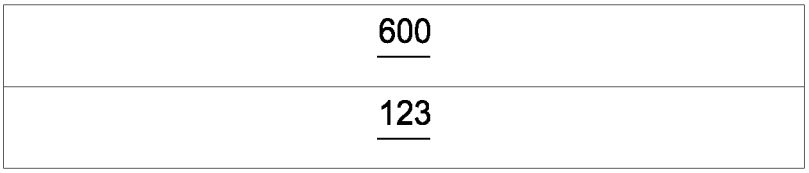

600
123

FIG. 6